

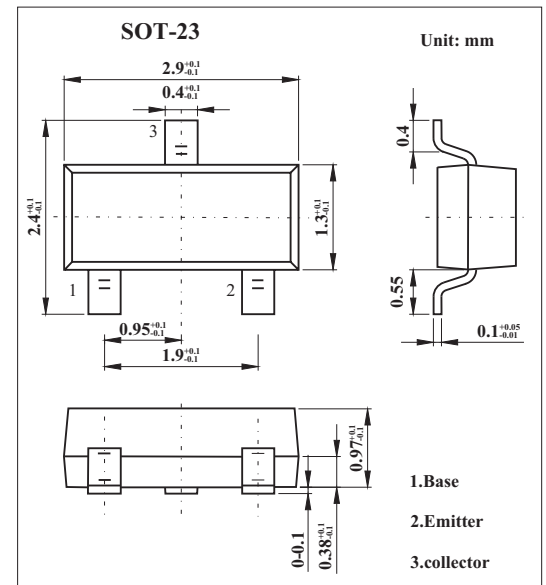
SOT-23 Plastic-Encapsulate Transistors

Features

- Collector current: $I_C = 0.5A$
- Weight: 0.080 grams (approx)
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to 150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -50mA$	200		350	
		$V_{CE} = -1V, I_C = -500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA, f = 30MHz$	150			MHz

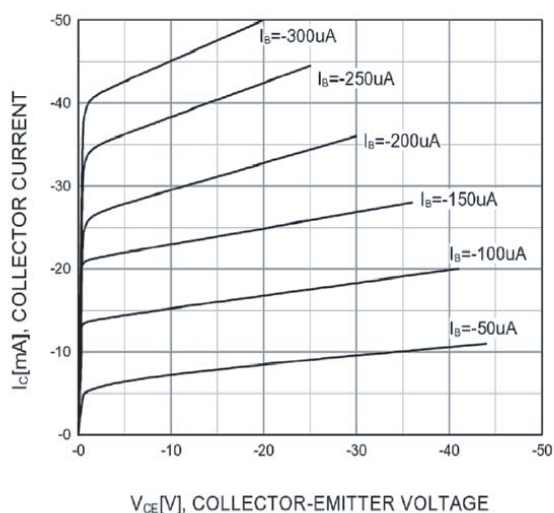
Marking

Marking	2TY
---------	-----

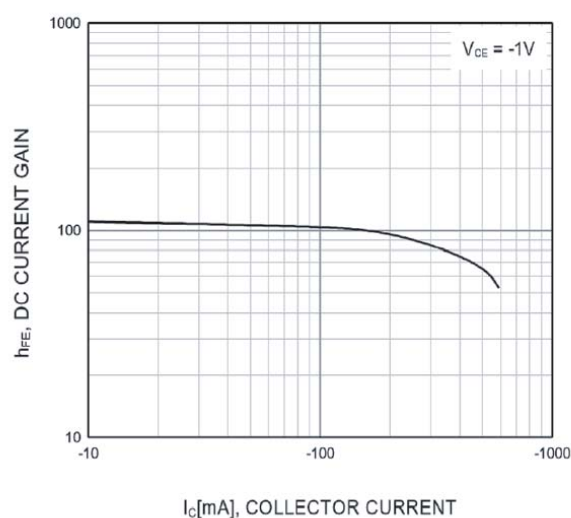


RATINGS AND CHARACTERISTIC CURVES

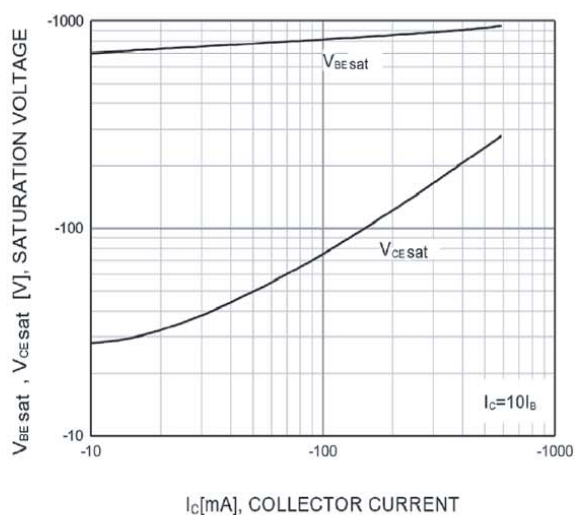
■ Typical Characteristics



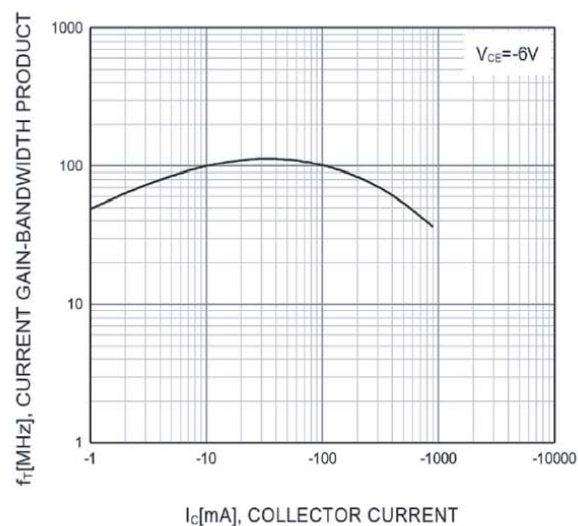
Static Characteristic



DC current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product